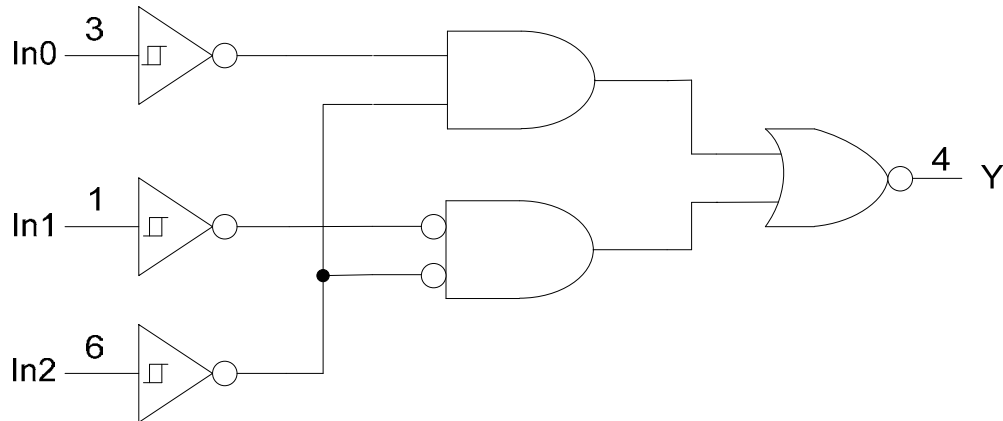


Pin Descriptions

Pin Name	Function
IN1	Data Input
GND	Ground
IN0	Data Input
Y	Data Output
V _{CC}	Supply Voltage
IN2	Data Input

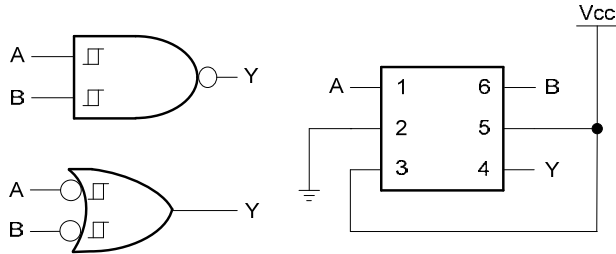
Logic Diagram



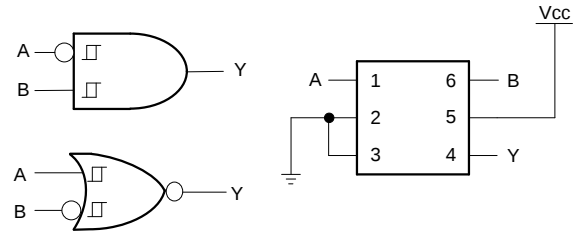
Function Table

Inputs			Output
IN2	IN1	IN0	Y
L	L	L	L
L	L	H	H
L	H	L	L
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	L
H	H	H	L

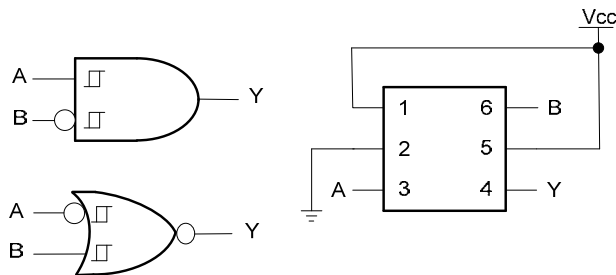
Logic Configurations



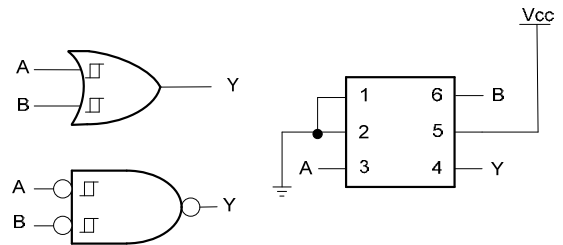
Configuration 1
2-Input NAND Gate
2-Input OR Gate with Both Inputs Inverted



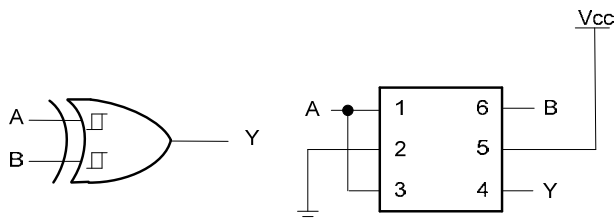
Configuration 2
2-Input AND Gate with A Input Inverted
2-Input NOR Gate with B Input Inverted



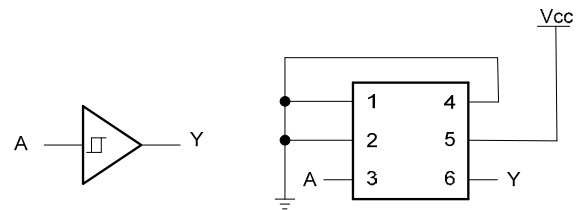
Configuration 3
2-Input AND Gate with B Input Inverted
2-Input NOR Gate with A Input Inverted



Configuration 4
2-Input OR Gate
2-Input NAND Gate with Both Inputs Inverted



Configuration 5
2-Input XOR Gate



Configuration 6
Buffer

Function Selection Table	
Logic Function	Configuration
2-input NAND	1
2-input NAND with both inputs inverted	4
2-input AND with inverted input	2, 3
2-input NOR with inverted input	2, 3
2-input OR	4
2-input OR with both inputs inverted	1
2-input XOR	5
1-input Buffer	6

Absolute Maximum Ratings (Note 4)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to 6.5	V
V _I	Input Voltage Range	-0.5 to 6.5	V
V _O	Voltage applied to output in high impedance or I _{OFF} State	-0.5 to 6.5	V
V _O	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I < 0	-50	mA
I _{OK}	Output Clamp Current	-50	mA
I _O	Continuous output current	±50	mA
	Continuous current through V _{DD} or GND	±100	mA
T _J	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 5)

Symbol	Parameter		Min	Max	Unit
V _{CC}	Operating Voltage	Operating	1.65	5.5	V
		Data retention only	1.5		V
V _I	Input Voltage		0	5.5	V
V _O	Output Voltage		0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.65V		-4	mA
		V _{CC} = 2.3V		-8	
		V _{CC} = 3V		-16	
				-24	
		V _{CC} = 4.5V		-32	
I _{OL}	Low-level output current	V _{CC} = 1.65V		4	mA
		V _{CC} = 2.3V		8	
		V _{CC} = 3V		16	
				24	
		V _{CC} = 4.5V		32	
Δt/ΔV	Input transition rise or fall rate	V _{CC} = 1.8V ± 0.15V, 2.5V ± 0.2V		20	ns/V
		V _{CC} = 3.3V ± 0.3V		10	
		V _{CC} = 5V ± 0.5V		5	
T _A	Operating free-air temperature		-40	+125	°C

Notes: 5. Unused inputs should be held at V_{CC} or Ground.

Electrical Characteristics $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$ (All typical values are at $V_{CC} = 3.3\text{V}$, $T_A = +25^{\circ}\text{C}$)

Symbol	Parameter	Test Conditions	V_{CC}	Min	Typ	Max	Unit
V_{T+}	Positive-going input threshold voltage		1.65V	0.70		1.20	
			2.3V	1.11		1.60	
			3V	1.50		2.00	
			4.5V	2.16		2.74	
			5.5V	2.61		3.33	
V_{T-}	Negative-going input threshold voltage		1.65V	0.30		0.72	
			2.3V	0.58		1.00	
			3V	0.80		1.30	
			4.5V	1.21		1.95	
			5.5V	1.45		2.35	
ΔV_T	Hysteresis ($V_{T+} - V_{T-}$)		1.65V	0.30		0.62	
			2.3V	0.40		0.80	
			3V	0.35		1.00	
			4.5V	0.55		1.10	
			5.5V	0.60		1.20	
V_{OH}	High Level Output Voltage	$I_{OH} = -100\mu\text{A}$	1.65V to 5.5V	$V_{CC} - 0.1$			V
		$I_{OH} = -4\text{mA}$	1.65V	1.2			
		$I_{OH} = -8\text{mA}$	2.3V	1.9			
		$I_{OH} = -16\text{mA}$	3V	2.4			
		$I_{OH} = -24\text{mA}$		2.3			
		$I_{OH} = -32\text{mA}$	4.5V	3.8			
V_{OL}	High-level Input Voltage	$I_{OL} = 100\mu\text{A}$	1.65V to 5.5V			0.1	V
		$I_{OL} = 4\text{mA}$	1.65V			0.45	
		$I_{OL} = 8\text{mA}$	2.3V			0.3	
		$I_{OL} = 16\text{mA}$	3V			0.4	
		$I_{OL} = 24\text{mA}$				0.55	
		$I_{OL} = 32\text{mA}$	4.5			0.55	
I_I	Input Current	$V_I = 5.5\text{V}$ or GND	0 to 5.5V			± 5	μA
I_{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5\text{V}$	0			± 10	μA
I_{CC}	Supply Current	$V_I = 5.5\text{V}$ of GND $I_O = 0$	1.65V to 5.5V			10	μA
ΔI_{CC}	Additional Supply Current	One input at $V_{CC} - 0.6\text{V}$ Other inputs at V_{CC} or GND	3V to 5.5V			500	μA

Electrical Characteristics $T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ (All typical values are at $V_{CC} = 3.3\text{V}$, $T_A = +25^{\circ}\text{C}$)

Symbol	Parameter	Test Conditions	V_{CC}	Min	Typ	Max	Unit
V_{T+}	Positive-going input threshold voltage		1.65V	0.70		1.20	
			2.3V	1.11		1.60	
			3V	1.50		2.00	
			4.5V	2.16		2.74	
			5.5V	2.61		3.33	
V_{T-}	Negative-going input threshold voltage		1.65V	0.30		0.75	
			2.3V	0.58		1.03	
			3V	0.80		1.33	
			4.5V	1.21		1.95	
			5.5V	1.45		2.35	
ΔV_T	Hysteresis ($V_{T+} - V_{T-}$)		1.65V	0.30		0.62	
			2.3V	0.37		0.80	
			3V	0.32		1.00	
			4.5V	0.50		1.20	
			5.5V	0.55		1.40	
V_{OH}	High Level Output Voltage	$I_{OH} = -100\mu\text{A}$	1.65V to 5.5V	$V_{CC} - 0.1$			V
		$I_{OH} = -4\text{mA}$	1.65V	0.95			
		$I_{OH} = -8\text{mA}$	2.3V	1.7			
		$I_{OH} = -16\text{mA}$	3V	1.9			
		$I_{OH} = -24\text{mA}$		2.0			
		$I_{OH} = -32\text{mA}$	4.5V	3.4			
V_{OL}	High-level Input Voltage	$I_{OL} = 100\mu\text{A}$	1.65V to 5.5V			0.1	V
		$I_{OL} = 4\text{mA}$	1.65V			0.7	
		$I_{OL} = 8\text{mA}$	2.3V			0.45	
		$I_{OL} = 16\text{mA}$	3V			0.6	
		$I_{OL} = 24\text{mA}$				0.8	
		$I_{OL} = 32\text{mA}$	4.5			0.8	
I_I	Input Current	$V_I = 5.5\text{V}$ or GND	0 to 5.5V			± 100	μA
I_{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5\text{V}$	0			± 200	μA
I_{CC}	Supply Current	$V_I = 5.5\text{V}$ of GND $I_O = 0$	1.65V to 5.5V			200	μA
ΔI_{CC}	Additional Supply Current	One input at $V_{CC} - 0.6\text{V}$ Other inputs at V_{CC} or GND	3V to 5.5V			5000	μA

Electrical Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^\circ C$)

Symbol	Parameter	Test Conditions	V_{CC}	Min	Typ	Max	Unit
C_I	Input Capacitance	$V_I = V_{CC} - \text{or GND}$	3.3		3.5		pF
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT26	(Note 6)		204		$^\circ C/W$
		SOT363			371		
		X2-DFN1410-6			430		
		X2-DFN1010-6			510		
θ_{JC}	Thermal Resistance Junction-to-Case	SOT26	(Note 6)		52		$^\circ C/W$
		SOT363			143		
		X2-DFN1410-6			190		
		X2-DFN1010-6			250		

Notes: 6. Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Switching Characteristics

$T_A = -40^\circ C$ to $+85^\circ C$, $C_L = 30$ or $50pF$ as noted (see Figure 1)

Parameter	From (Input)	TO (OUTPUT)	$V_{CC} = 1.8V \pm 0.15V$		$V_{CC} = 2.5V \pm 0.2V$		$V_{CC} = 3.3V \pm 0.3V$		$V_{CC} = 5V \pm 0.5V$		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{pd}	Any	Y	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

$T_A = -40^\circ C$ to $+125^\circ C$, $C_L = 30$ or $50pF$ as noted (see Figure 1)

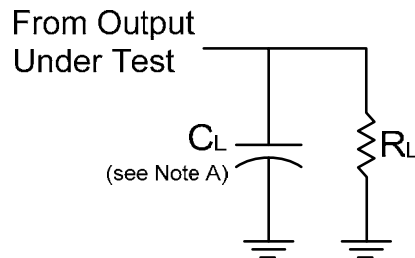
Parameter	From (Input)	TO (OUTPUT)	$V_{CC} = 1.8V \pm 0.15V$		$V_{CC} = 2.5V \pm 0.2V$		$V_{CC} = 3.3V \pm 0.3V$		$V_{CC} = 5V \pm 0.5V$		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	
t_{pd}	Any	Y	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

Operating Characteristics

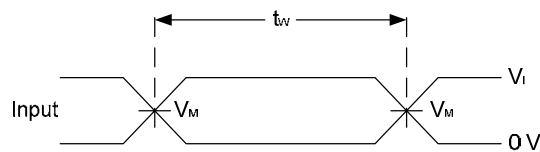
$T_A = +25^\circ C$

Parameter		Test Conditions	$V_{CC} = 1.8V$	$V_{CC} = 2.5V$	$V_{CC} = 3.3V$	$V_{CC} = 5V$	Unit
			Typ.	Typ.	Typ.	Typ.	
C_{pd}	Power dissipation capacitance	$f = 10 \text{ MHz}$	22	22	23	24	pF

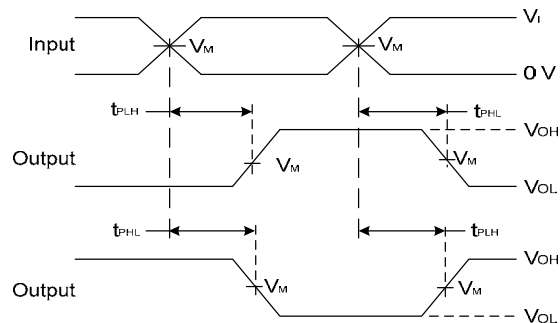
Parameter Measurement Information



V_{CC}	Inputs		V_M	C_L	R_L
	V_I	t_r/t_f			
$1.8V \pm 0.15V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	30pF	1K Ω
$2.5V \pm 0.2V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	30pF	500 Ω
$3.3V \pm 0.3V$	3V	$\leq 2.5ns$	1.5V	50pF	500 Ω
$5V \pm 0.5V$	V_{CC}	$\leq 2.5ns$	$V_{CC}/2$	50pF	500 Ω



**Voltage Waveform
Pulse Duration**

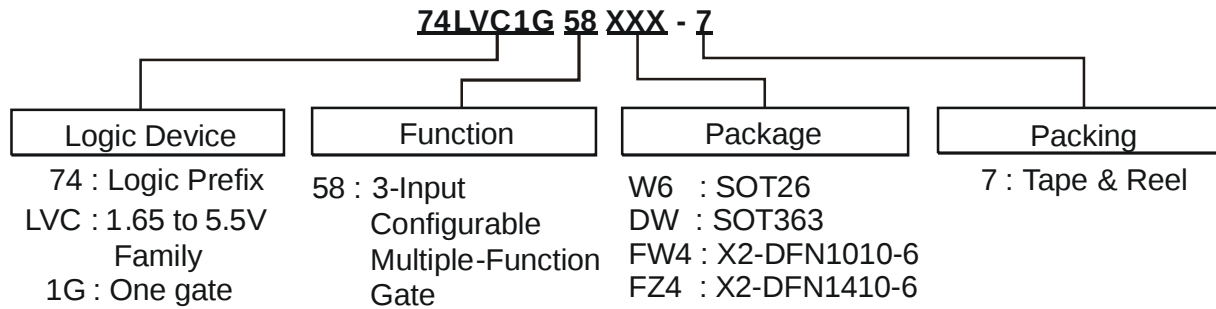


**Voltage Waveform
Propagation Delay Times
Inverting and Non Inverting Outputs**

Figure 1. Load Circuit and Voltage Waveforms

- Notes:
- A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate ≤ 10 MHz
 - C. Inputs are measured separately one transition per measurement
 - D. t_{PLH} and t_{PHL} are the same as t_{PD}

Ordering Information

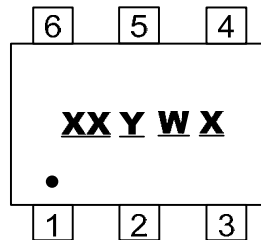


Device	Package Code	Packaging (Note 7)	7" Tape and Reel	
			Quantity	Part Number Suffix
 74LVC1G58W6-7	W6	SOT26	3000/Tape & Reel	-7
 74LVC1G58DW-7	DW	SOT363	3000/Tape & Reel	-7
 74LVC1G58FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
 74LVC1G58FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Marking Information

(1) SOT26, SOT363

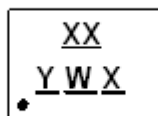


XX : Identification code
Y : Year 0~9
W : Week : A~Z : 1~26 week;
a~z : 27~52 week; z represents
52 and 53 week
X : A~Z : Internal Code

Part Number	Package	Identification Code
74LVC1G58W6	SOT26	TX
74LVC1G58DW	SOT363	TX

(2) X2-DFN1010-6, X2-DFN1410-6

(Top View)

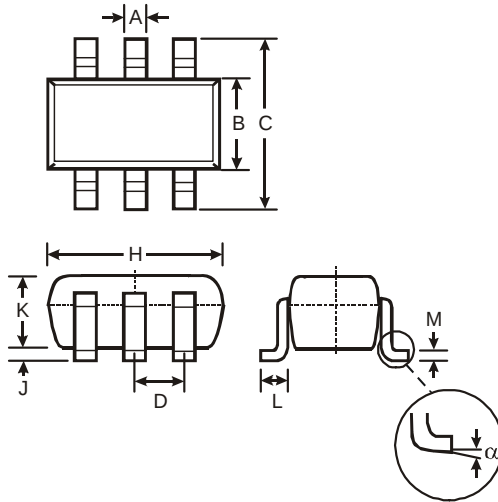


XX : Identification Code
Y : Year : 0~9
W : Week : A~Z : 1~26 week;
a~z : 27~52 week; z represents
52 and 53 week
X : A~Z : Internal code

Part Number	Package	Identification Code
74LVC1G58FW4	X2-DFN1010-6	TX
74LVC1G58FZ4	X2-DFN1410-6	TX

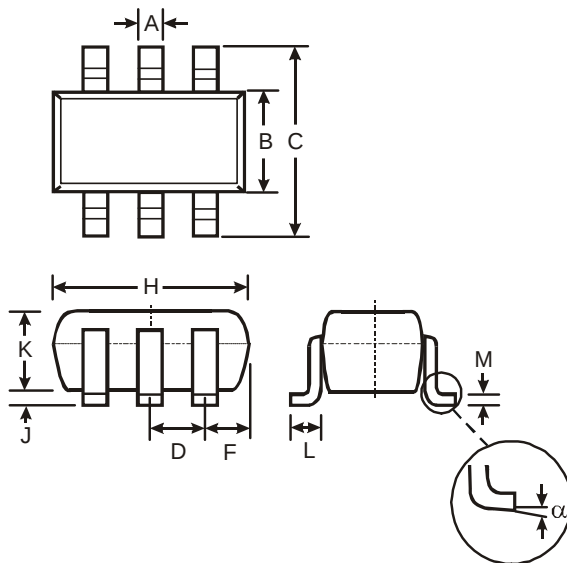
Package Outline Dimensions (All Dimensions in mm)

(1) SOT26



SOT26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

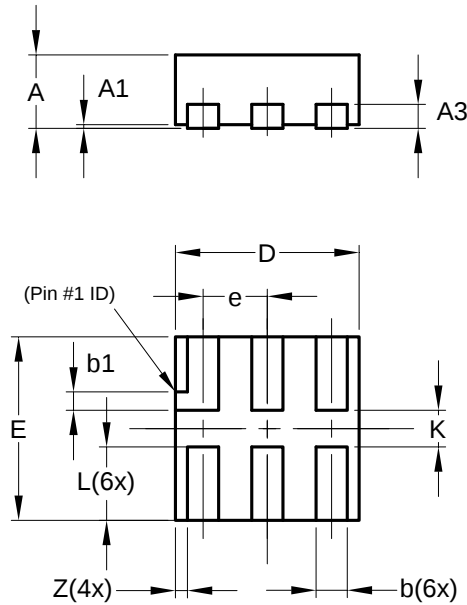
(2) SOT363



SOT363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

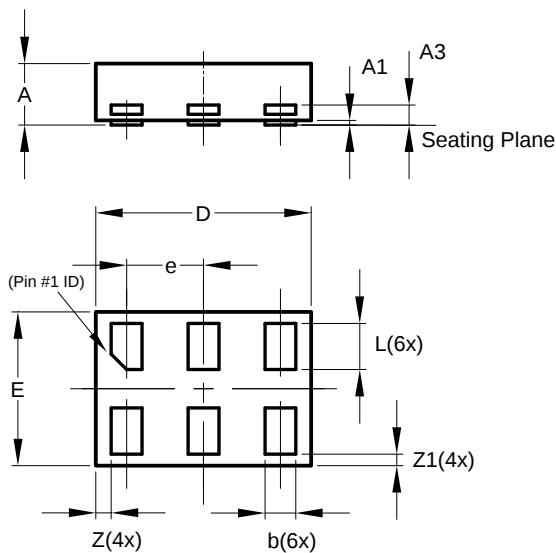
Package Outline Dimensions (All Dimensions in mm)

(3) X2-DFN1010-6



X2-DFN1010-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.14	0.20	0.17
b1	0.05	0.15	0.10
D	0.95	1.05	1.00
E	0.95	1.05	1.00
e	—	—	0.35
L	0.35	0.45	0.40
K	0.15	—	—
Z	—	—	0.065
All Dimensions in mm			

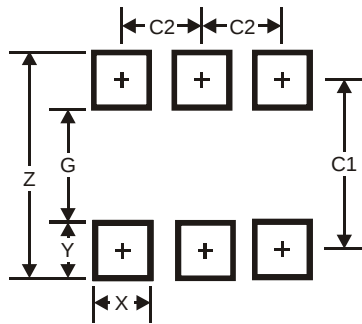
(4) X2-DFN1410-6



X2-DFN1410-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
E	0.95	1.05	1.00
e	—	—	0.50
L	0.25	0.35	0.30
Z	—	—	0.10
Z1	0.045	0.105	0.075
All Dimensions in mm			

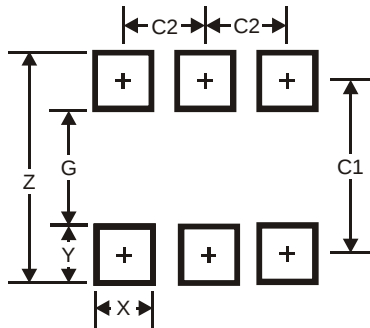
Suggest Pad Layout

(1) SOT26



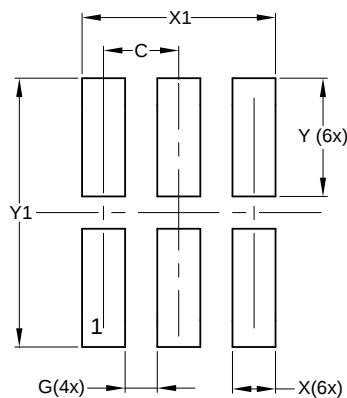
Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

(2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

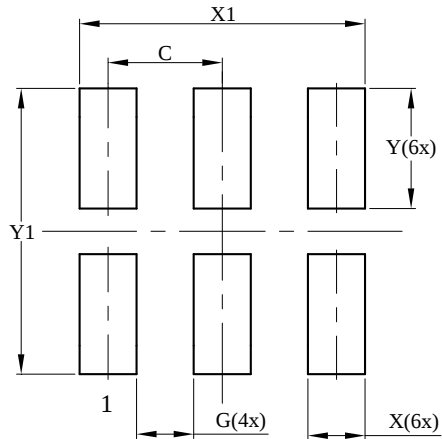
(3) X2-DFN1010-6



Dimensions	Value (in mm)
C	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

Suggest Pad Layout

(4) X2-DFN1410-6



Dimensions	Value (in mm)
C	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
Y1	1.250

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